

## AP50T10GP-HF-VB Datasheet

### N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY	
$V_{DS}$ (V)	100
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10$ V	0.036
$I_D$ (A) <sup>a</sup>	55
Configuration	Single

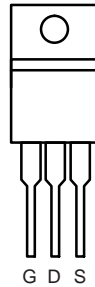
#### FEATURES

- TrenchFET<sup>®</sup> Power MOSFETS
- 175 °C Junction Temperature
- Low Thermal Resistance Package

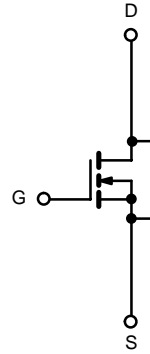


Available  
**RoHS\***  
 COMPLIANT

TO-220AB



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	100	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175$ °C)	$T_C = 25$ °C	$I_D$	55	A
	$T_C = 125$ °C		40	
Pulsed Drain Current		$I_{DM}$	135	
Avalanche Current		$I_{AR}$	35	
Repetitive Avalanche Energy <sup>a</sup>		$E_{AR}$	61	mJ
Maximum Power Dissipation <sup>a</sup>	$T_C = 25$ °C	$P_D$	127 <sup>b</sup>	W
	$T_A = 25$ °C <sup>c</sup>		3.75	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to 175	°C

#### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Limit	Unit
Junction-to-Ambient	(PCB Mount) <sup>c</sup>	$R_{thJA}$	40	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	1.4	

Notes:

a. Duty cycle  $\leq 1$  %.

b. See SOA curve for voltage derating.

c. When Mounted on 1" square PCB (FR-4 material).

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

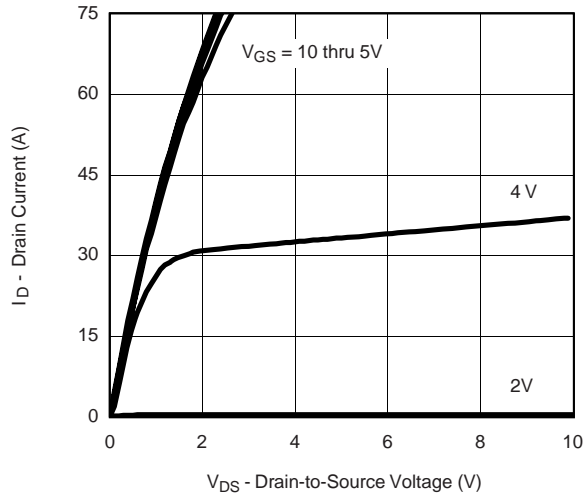
SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>SS</sub> = 0 V, I <sub>D</sub> = 250 μA	100			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1		3	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	75			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A		0.036		Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3 A		0.038		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A, T <sub>J</sub> = 125 °C		0.050		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A, T <sub>J</sub> = 175 °C		0.065		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A	10			S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		4500		pF
Output Capacitance	C <sub>oss</sub>			270		
Reverse Transfer Capacitance	C <sub>rss</sub>			90		
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A		35	60	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			11		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			9		
Gate Resistance	R <sub>G</sub>			1.7		Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 50 V, R <sub>L</sub> = 1.25 Ω I <sub>D</sub> ≅ 40 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 2.5 Ω		11	20	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			12	20	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			30	45	
Fall Time <sup>c</sup>	t <sub>f</sub>			12	20	
Source-Drain Diode Ratings and Characteristics T <sub>C</sub> = 25 °C <sup>b</sup>						
Continuous Current	I <sub>S</sub>				40	A
Pulsed Current	I <sub>SM</sub>				120	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V		1.0	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 30 A, di/dt = 100 A/μs		60	100	ns
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>			5	8	A
Reverse Recovery Charge	Q <sub>rr</sub>				0.15	0.4

Notes:

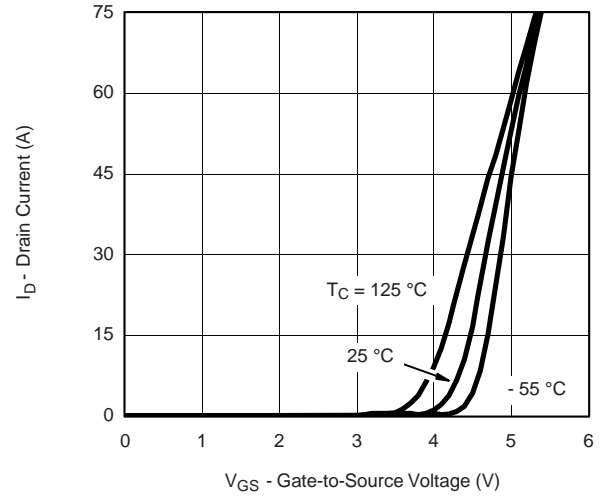
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
 b. Guaranteed by design, not subject to production testing.  
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



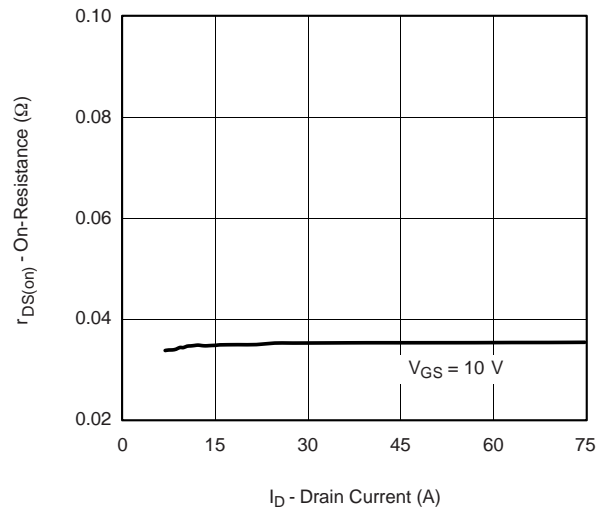
**Output Characteristics**



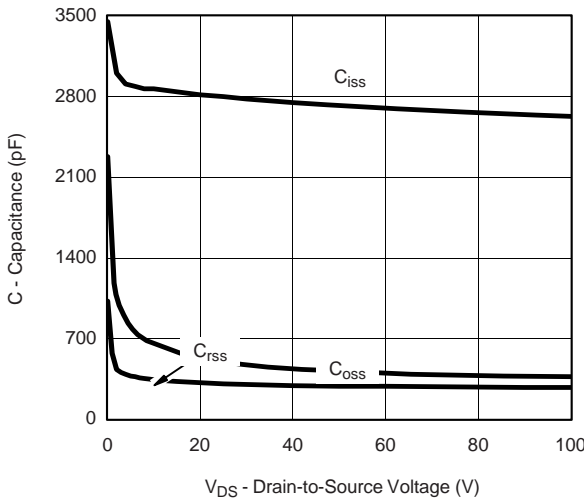
**Transfer Characteristics**



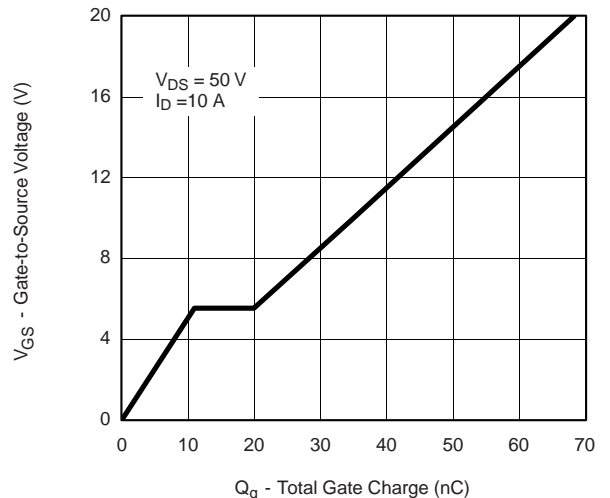
**Transconductance**



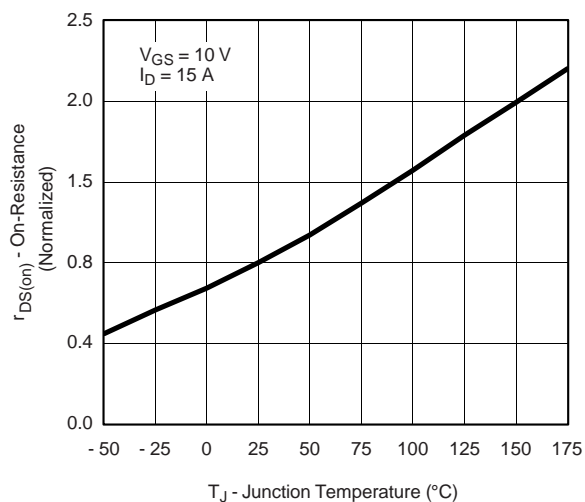
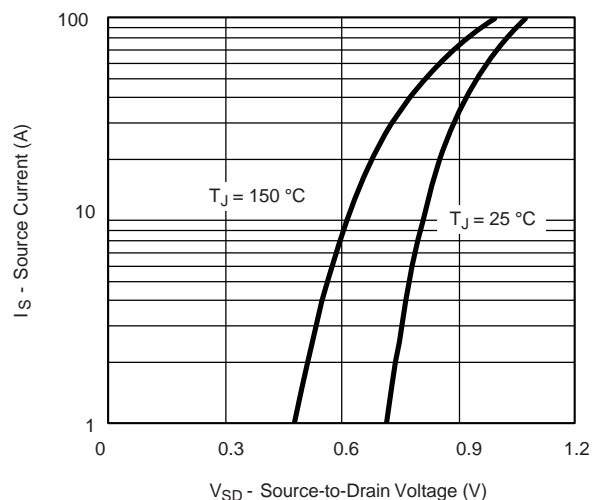
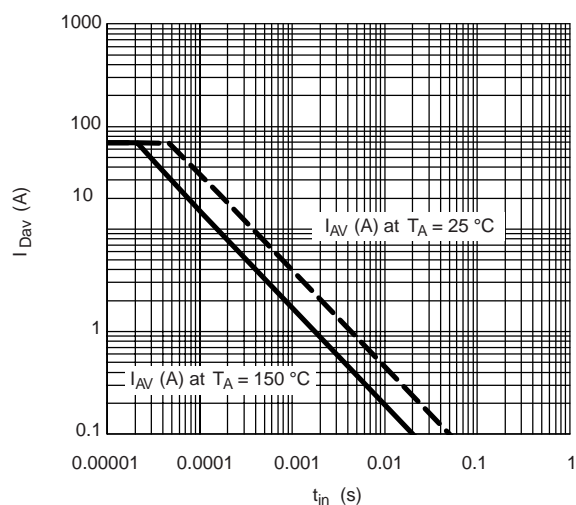
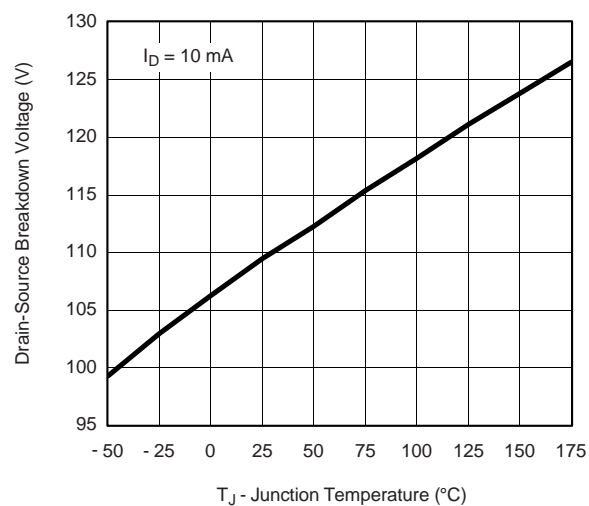
**On-Resistance vs. Drain Current**



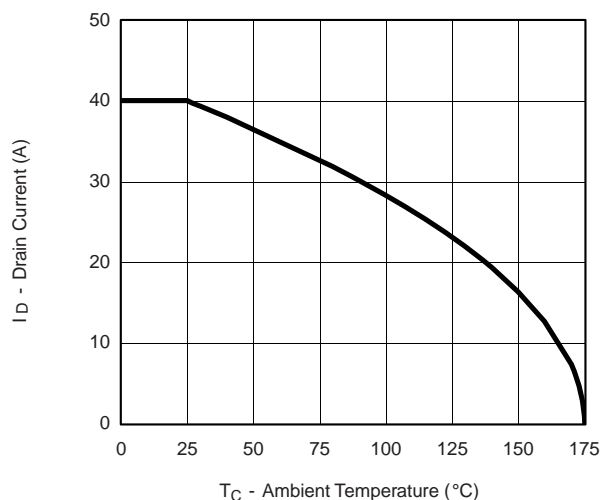
**Capacitance**



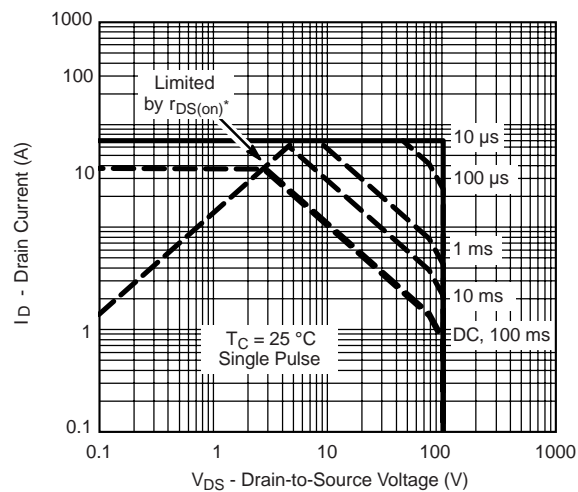
**Gate Charge**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

**On-Resistance vs. Junction Temperature**

**Source-Drain Diode Forward Voltage**

**Avalanche Current vs. Time**

**Drain-Source Breakdown Voltage vs. Junction Temperature**

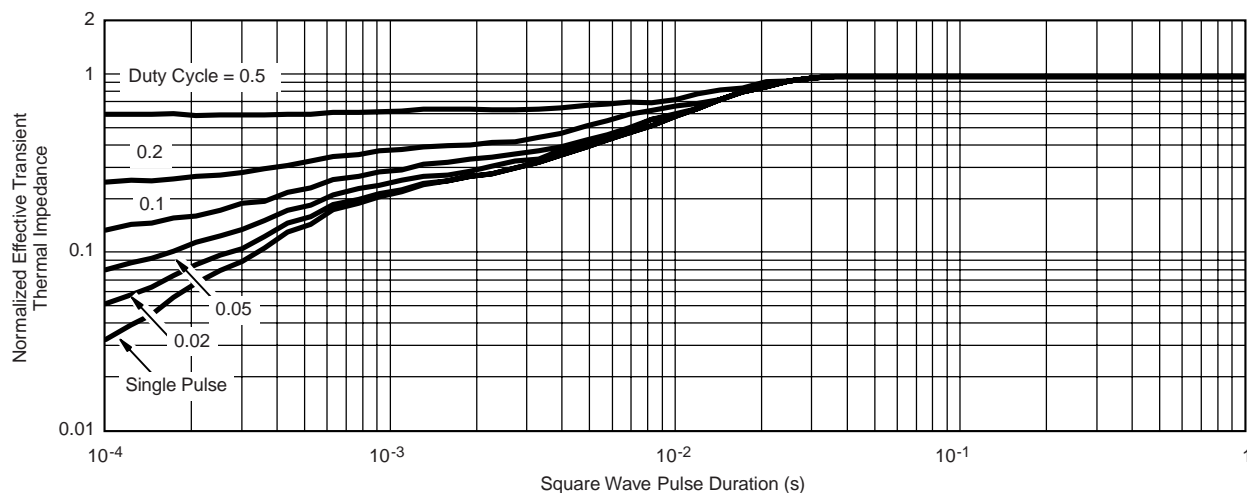
## THERMAL RATINGS



**Maximum Avalanche and Drain Current  
vs. Case Temperature**

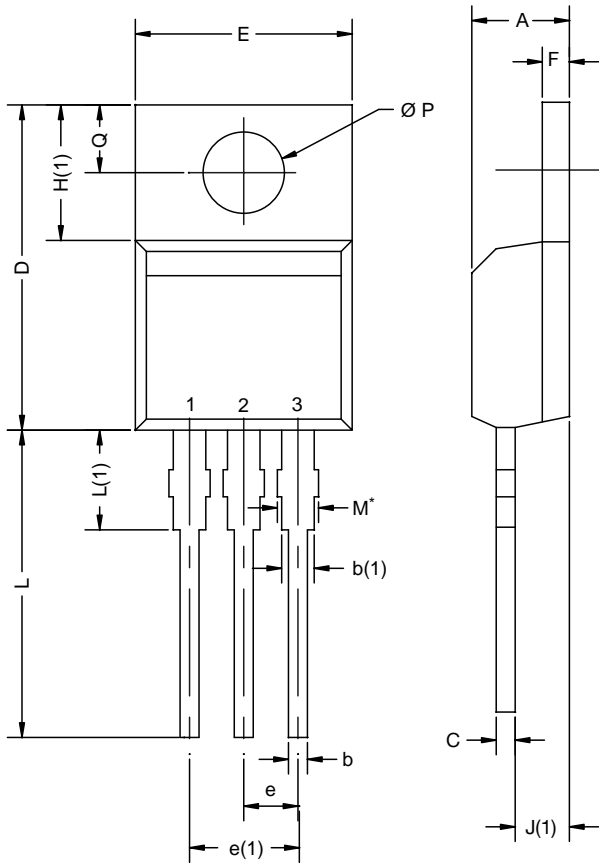


**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Case**

## TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: X12-0208-Rev. N, 08-Oct-12				
DWG: 5471				

### Notes

\* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM

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